

Docket No.: M4065.1006/P1006-B  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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In re Patent Application of:  
Terry L. Gilton

Application No.: 10/618,824

Group Art Unit: N/A

Filed: July 14, 2003

Examiner: Not Yet Assigned

For: PROGRAMMABLE CONDUCTOR  
MEMORY CELL STRUCTURE AND  
METHOD THEREFOR

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**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

Those patents and publications which are marked with an asterisk (\*) in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application no. 10/121,790, filed April 10, 2002, and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

A brief explanation of relevance of the non-U.S. patent documents listed on form PTO/SB/08 is provided and attached hereto as Appendix A. The brief explanation provided for each document is not tantamount to an admission that a document is

“material” or that it qualifies as prior art. The Examiner is respectfully requested to utilize Appendix A only as a tool by which to better categorize the documents for substantive use in examining the claims of the application.

Documents discussed in Appendix A marked with an asterisk (\*\*) are indicated to be potentially more relevant than others. Such marking is provided only to assist the Examiner; however, the Examiner is requested to thoroughly review all documents cited herein.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that the Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

The Commissioner is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.1006/P1006-A. A duplicate copy of this paper is enclosed.

Dated: February 27, 2004

Respectfully submitted,

By 

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	Not Yet Assigned
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				First Named Inventor	Terry L. Gilton
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
*	AA	2002/0000666	1/2002	Kozicki et al.	
*	AB	2002/0072188	6/2002	Gilton	
*	AC	2002/0106849	08/2002	Moore	
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				Art Unit	N/A
				Examiner Name	Not Yet Assigned
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Page Count
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
*	BA	JP-56126916	10/1981	Akira et al.		
*	BB	WO 97/48032	12/18/1997	Kozicki et al.		
*	BC	WO 99/28914	06/10/1999	Kozicki et al.		
*	BD	WO 00/48196	8/17/00	Arizona Board of Regents		
*	BE	WO 02/21542-A1	3/14/02	Axon Technologies Corp.		

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/618,824
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				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>	
*	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.		
*	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.		
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*	CD	Affi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.		
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*	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
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*	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
*	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.		
*	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
*	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
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*	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
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Sheet	6	of	12	Attorney Docket Number	M4065.1006/P1006-B

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Examiner Signature		Date Considered	
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